ABSTRACT OF THE DISCLOSURE

A method for fabricating a semiconductor substrate comprises the steps of employing a diffusion method to diffuse, in a silicon substrate, an element, which is capable of controlling a conductive type, and to form a diffused region, forming a porous layer in the diffused region, forming a non-porous single crystal layer on the porous layer, bonding the non-porous single crystal layer to a base substrate, while an insulation layer is provided either on a surface to be bonded of the non-porous single crystal layer or on a surface to be bonded of the base substrate, and removing the porous layer.

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